

Masatoshi Kotera

List of Publications by Year in descending order

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48
papers

397
citations

933447

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752698

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48
all docs

48
docs citations

48
times ranked

104
citing authors

#	ARTICLE	IF	CITATIONS
1	Investigation of non-charging exposure conditions for insulating resist films in electron beam lithography. Japanese Journal of Applied Physics, 2021, 60, SCCB02.	1.5	1
2	Non-charging Conditions of Insulating Film under Electron Beam Irradiation. E-Journal of Surface Science and Nanotechnology, 2020, 18, 106-109.	0.4	3
3	Measurement of fogging electrons present in scanning electron microscope specimen chamber. Japanese Journal of Applied Physics, 2020, 59, SIIB01.	1.5	2
4	Simulation of fogging electron trajectories in a scanning electron microscope. , 2018, , .		1
5	PM-26Dependence of the Flare Electron on Accelerating Voltage in Scanning Electron Microscope. Microscopy (Oxford, England), 2017, 66, i30-i30.	1.5	0
6	Multiphysics Simulation of Nanopatterning in Electron Beam Lithography. Journal of Photopolymer Science and Technology = [Fotoporima Konwakai Shi], 2016, 29, 725-730.	0.3	3
7	Measurement of surface potential of insulating film on a conductive substrate in a scanning electron microscope specimen chamber. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, 06F316.	1.2	9
8	Analysis of Resist Surface Deformation during Electron Beam Irradiation. Japanese Journal of Applied Physics, 2010, 49, 06GE08.	1.5	7
9	Simulation of Fogging Electrons in Electron Beam Lithography. Japanese Journal of Applied Physics, 2009, 48, 06FB05.	1.5	11
10	Development of new bio-electron microscope that uses DLC film. Diamond and Related Materials, 2009, 18, 1019-1022.	3.9	2
11	Extreme Ultraviolet Lithography Simulation by Tracing Photoelectron Trajectories in Resist. Japanese Journal of Applied Physics, 2008, 47, 4944-4949.	1.5	5
12	Time-dependent charge distributions in polymer films under electron beam irradiation. Journal of Applied Physics, 2008, 104, .	2.5	13
13	Collection field dependence of charging-up of insulators in low voltage scanning electron microscope. , 2007, , .		2
14	Photoelectron trajectory simulation in a resist for EUV lithography. , 2007, , .		0
15	Influence of Electron Scattering on Resist Pattern Edge Roughness in Low Dose Electron Beam Lithography. Zairyo/Journal of the Society of Materials Science, Japan, 2006, 55, 177-182.	0.2	0
16	Precision Analysis of Electron Beam Lithography. IEEJ Transactions on Electronics, Information and Systems, 2006, 126, 683-689.	0.2	1
17	Deposited Energy Dependence of Surface Roughness of Polymethylmethacrylate Irradiated by Electron Beam. Japanese Journal of Applied Physics, 2005, 44, 5595-5599.	1.5	1
18	Influence of Electron Scattering on Resolution in Low-Dose Electron-Beam Lithography. Japanese Journal of Applied Physics, 2004, 43, 3749-3754.	1.5	4

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19	Impacts of 30-nm-thick resist on improving resolution performance of low-energy electron beam lithography. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 3518.	1.6	1
20	Calculation of Coulomb Interaction among Electrons in a High-Current Electron-Beam Exposure System. Japanese Journal of Applied Physics, 2004, 43, 3744-3748.	1.5	1
21	Mask Charging Phenomena during Electron Beam Exposure in the EPL System. Microscopy and Microanalysis, 2004, 10, 771-775.	0.4	0
22	Line Edge Roughness of Developed Resist with Low-Dose Electron Beam Exposure. Japanese Journal of Applied Physics, 2002, 41, 4150-4156.	1.5	20
23	A Monte Carlo study of spin-polarized electron backscattering from gold thin films. Nuclear Instruments & Methods in Physics Research B, 2001, 183, 196-202.	1.4	3
24	Simulation of time-dependent charging of resist on Si under electron-beam irradiation. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2001, 19, 2516.	1.6	15
25	Influence of Electron Density Distribution at the Electron Source in a Projection Exposure System. Japanese Journal of Applied Physics, 2001, 40, 904-909.	1.5	2
26	Performance evaluation of the multi-stage Mott polarimeter using the Monte Carlo simulation. Review of Scientific Instruments, 2001, 72, 3921-3926.	1.3	1
27	An Improved Electron Scattering Simulation at the Mask in a Projection Lithography System. Japanese Journal of Applied Physics, 2000, 39, 6861-6868.	1.5	5
28	The Simulation of Charging-up of Insulator under Electron Beam Irradiation.. Shinku/Journal of the Vacuum Society of Japan, 2000, 43, 151-156.	0.2	0
29	Analysis of Magnetic-domain Contrast of the Spin-SEM.. Shinku/Journal of the Vacuum Society of Japan, 2000, 43, 259-262.	0.2	0
30	Characteristic Variation of Exposure Pattern in Cell-Projection Electron-Beam Lithography. Japanese Journal of Applied Physics, 1999, 38, 7031-7034.	1.5	6
31	Dynamic Simulation of Electron-Beam-Induced Chargingup of Insulators. Japanese Journal of Applied Physics, 1999, 38, 7176-7179.	1.5	38
32	Study on Sensitization of the Mott Polarimeter.. Shinku/Journal of the Vacuum Society of Japan, 1999, 42, 361-364.	0.2	0
33	Development of a Simulator for Cell-projection Type Electron Beam Lithography.. Shinku/Journal of the Vacuum Society of Japan, 1999, 42, 764-767.	0.2	0
34	Analysis of the Image Formation Mechanism on High Energy Scanning Electron Microscopy. Japanese Journal of Applied Physics, 1998, 37, 7024-7027.	1.5	2
35	Application of an oligo-scattering beam to an electron beam analyzer for observing specimens in air: Monte Carlo simulation of an oligo-scattering beam. Electronics and Communications in Japan, 1997, 80, 1-11.	0.2	1
36	Performance Analysis of the Mott Polarimeter.. Shinku/Journal of the Vacuum Society of Japan, 1997, 40, 173-176.	0.2	0

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37	Analysis of Surface Magnetic Structure Using Type-I Magnetic Contrast in the Scanning Electron Microscope.. Shinku/Journal of the Vacuum Society of Japan, 1997, 40, 190-192.	0.2	0
38	Evaluation of the Mott Polarimeter in the Electron Spin Polarization Scanning Electron Microscopy. Japanese Journal of Applied Physics, 1996, 35, 6614-6619.	1.5	7
39	Analysis of Charging Effect During Observation of Trench Structures by Scanning Electron Microscope. Japanese Journal of Applied Physics, 1994, 33, 7144-7147.	1.5	20
40	Computer simulation of light emission by high-energy electrons in YAG single crystals. Ultramicroscopy, 1994, 54, 293-300.	1.9	12
41	Applications of a direct simulation of electron scattering to quantitative electron-probe microanalysis. Proceedings Annual Meeting Electron Microscopy Society of America, 1992, 50, 1670-1671.	0.0	0
42	Theoretical Evaluation of a Topographic Contrast of Scanning Electron Microscope Images. Japanese Journal of Applied Physics, 1991, 30, 3287-3293.	1.5	10
43	A Simulation of Electron Scattering in Metals. Japanese Journal of Applied Physics, 1990, 29, 2277-2282.	1.5	42
44	Secondary Electron Image Contrast in the Scanning Electron Microscope. Proceedings Annual Meeting Electron Microscopy Society of America, 1990, 48, 410-411.	0.0	0
45	A Monte Carlo Simulation of Secondary Electron Trajectories in a Specimen. Japanese Journal of Applied Physics, 1989, 28, 148-149.	1.5	3
46	Quantitative electron microprobe analysis of thin films on substrates with a new Monte Carlo simulation. Journal of Applied Physics, 1983, 54, 1110-1114.	2.5	29
47	Monte Carlo simulation of 10 keV electron scattering in a gold target. Journal of Applied Physics, 1981, 52, 997-1003.	2.5	84
48	Monte Carlo simulation of 10 keV electron scattering in an aluminum target. Journal of Applied Physics, 1981, 52, 7403-7408.	2.5	30